SEMICONDUCTOR FILM COMPOSITION, METHOD FOR MANUFACTURING SEMICONDUCTOR FILM COMPOSITION, METHOD FOR MANUFACTURING SEMICONDUCTOR MEMBER, METHOD FOR MANUFACTURING SEMICONDUCTOR PROCESSING MATERIAL, AND SEMICONDUCTOR DEVICE

ABSTRACT

Provided is a composition for forming a film for semiconductor devices, including: a compound (A) including a Si-O bond and a cationic functional group containing at least one of a primary nitrogen atom or a secondary nitrogen atom; a crosslinking agent (B) which includes three or more -C(=O)OX groups (X is a hydrogen atom or an alkyl group having from 1 to 6 carbon atoms) in the molecule, in which from one to six of three or more -C(=O)OX groups are -C(=O)OH groups, and which has a weight average molecular weight of from 200 to 600; and a polar solvent (D).